### **Channeling 2010**

Deflection of high-energy negative particles in a bent crystal through axial channeling and multiple volume reflection stimulated by doughnut scattering

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#### Outlook

- Deflection of high energy negative particles through interaction with crystalline axis
- boughnut scattering of particles in straight crystal
- Doughnut scattering of particles in bent crystal
- Experimental apparatus
- Deflection in DSB regime for perfect alignment with axis
- Interesting peculiarity vertical beam deflection
  - Deflection for orientations far from a perfect alignment



# Deflection of particle beams through interaction with crystalline axis

We observed deflection of 150 GeV  $\pi$ - by the <111> axis of a bent silicon crystal through different mechanisms

1. multiple scattering of  $\pi$ -mesons by bent atomic strings:

**Doughnut Scattering Bound (DSB)**  $\rightarrow$  quasi-bound states, particles follows the bent axis

**Doughnut Scattering UnBound (DSUB)**  $\rightarrow$  particles don't follow the bend

2. Volume capture by crystal axis

3. Multiple volume reflection in one crystal, assisted by DSUB



#### Doughnut scattering of particles in straight crystal

Multiple scatterings by atomic strings particles with orientation angle  $\psi$  are distributed along a circle with the radius  $\psi$  around the axis direction. Therefore this scattering was called "doughnut scattering" (DS)

Crystal length required to obtain a full randomization of the transverse momentums of particles (equalization length) was suggested by Lindhard

$$\psi_1 = \sqrt{\frac{4Z_1Z_2e^2}{pvd}}, \qquad \lambda_1 = \lambda(\psi_1) = \frac{4}{\pi^2 N da \psi_1},$$

For 150 GeV  $\pi^-$  mesons in Si crystal along <111> axis  $\psi_1$ =33.8 µrad and  $\lambda_1$ =26.3 µm



#### Doughnut scattering of particles in bent crystal

**A)** Deflection condition of particles by a bent crystal through DS regime was formulated by Shulga and Greenenko

If this condition is satisfied, particles have time to "finish" the momentum randomization around the changing angular position of axis – quasibound states (DSB)

$$\overline{\psi^2} = \frac{\lambda L}{R^2} \le \psi_1^2$$

Randomization center of particle momentums is in the angular position of axis, it shifts with the penetration of a particle into a bent crystal

**B)** For unbound states of doughnut scattering (DSUB) randomization radius, determined by transverse particle momentum, changes with changing the angular position of axis



#### **Experimental apparatus**

Four microstrip silicon detectors, two upstream and two downstream of the crystal were used to measure the particle angles with resolution of  $\sigma_a$ =3 µrad



#### **Experimental apparatus**

#### Silicon strip crystal, anticlastic bending



- 70×8×0.3 mm<sup>3</sup> silicon strip was bent along its length
- Bend angle was measured with 400 GeV/c proton beam, α=185 µrad.

Condition for particle deflection in DSB regime was fulfilled

$$\overline{\psi^2} = 0.098 \psi_1^2$$

#### Searching for <111> axis



- Cradle scan
- Deflection in horizontal direction

• Deflection in vertical direction

#### Deflection in DSB regime for perfect alignment with axis

Only particles with divergence less than 10 µrad are selected



Distribution maximum at  $\theta_x < \alpha$  because of the crystal torsion Deflection efficiency  $P_d(\theta_x > 0) = 95.4 \%$ 2, 3 – simulation results 3 – for straight crystal

#### Interesting peculiarity – vertical beam deflection

Beam incident with  $\theta_{vo} \leq \psi_1$  is deflected to the vertical direction



#### Observation of volume capture of particles in DSB regime





Maximum in deflection angles is about zero

#### Deflection for orientations far from a perfect alignment

Beam incident angle  $\theta_{xo} \approx \alpha/2$ 



Hatched histogram is a distribution for amorphous orientation Deflection angle distribution is broadened three times with respect to amorphous alignment and centered at  $\theta_x=0$ 

#### Deflection for orientations far from a perfect alignment

#### Incident angle $\theta_{xo} > \alpha/2$

Maximum is on the side opposite to the bend at  $\theta_x$ =-88 µrad



Effect MVR OC occurs when  $\alpha:\theta_{xo}:\theta_{yo}=4:2:1$  and  $\theta_{yo}>>\psi_1$  $\theta_{yo}$  is about zero  $\rightarrow$  MVR OC cannot occur near the crystal entrance

## Analysis with depth penetration (simulation)

Particles obtain large vertical momentums and some negative deflections This leads to the realization of the MVR OC for a large part of the beam



So, due to doughnut scattering in unbound regime near the entrance particles perform MVR OC in the following layers of the crystal





### Thank you